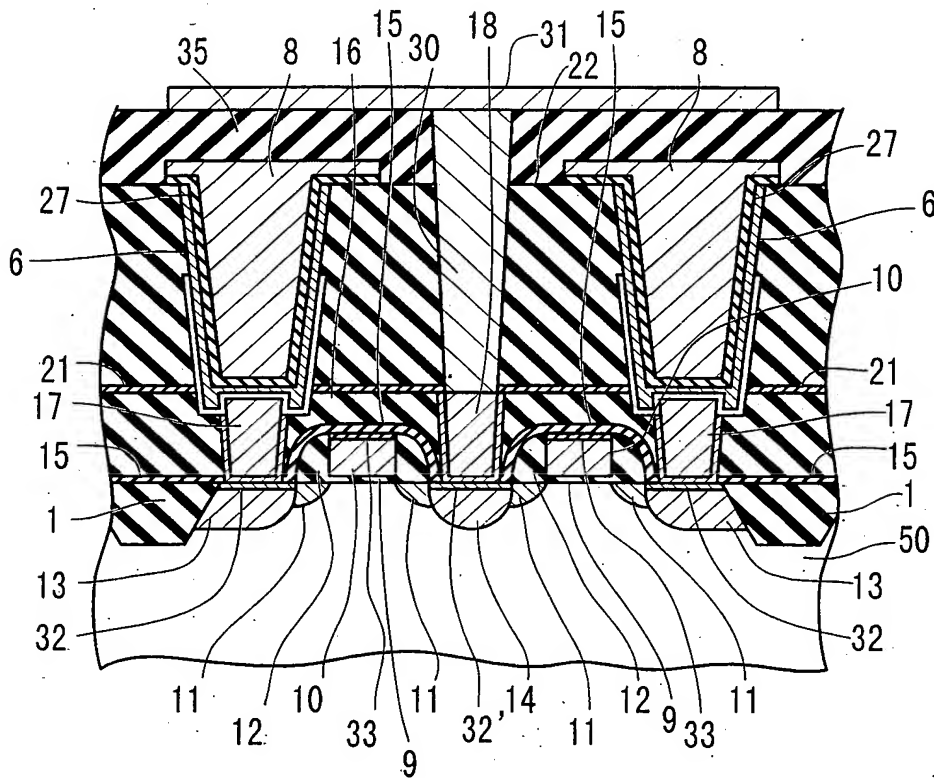
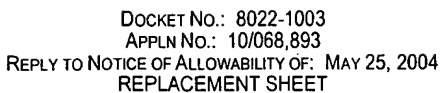




Fig. 2

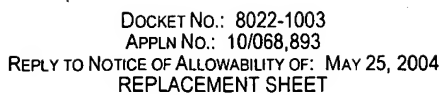




This diagram is a detailed cross-sectional view of a multi-layered structure, likely a semiconductor device or a specialized material stack. The structure is composed of several distinct layers and components, each identified by a numerical label:

- 13**: A central, thick layer with diagonal hatching, representing a substrate or a core material.
- 14**: A layer directly beneath the central layer 13, also with diagonal hatching but oriented differently.
- 15**: A thin, horizontal layer situated above the central layer 13.
- 16**: A layer above 15, featuring a series of rounded, protruding structures.
- 17** and **18**: Brackets at the top of the diagram grouping specific features into two main sections.
- 19** and **20**: Labels pointing to specific vertical structures or interfaces within the top layers of both the left and right sections.
- 21**: A layer above 16, showing a series of small, rectangular protrusions.
- 22**: The topmost layer of the structure, which appears to be a thin, uniform coating.
- 32** and **32'**: Labels at the bottom of the diagram, possibly indicating a base or a specific interface.
- 50**: A label on the right side, pointing to the outer boundary or a specific layer of the structure.

The diagram uses various hatching patterns (diagonal lines, cross-hatching, and solid black) to differentiate the materials and layers of the structure.



A detailed cross-sectional diagram of a device, likely a semiconductor component or a microfluidic chip. The device consists of a central rectangular cavity surrounded by a complex multi-layered structure. The top layer is indicated by label 8. Below it, there are several more layers, some of which are hatched with diagonal lines to represent different materials. Labels 28 and 29 point to specific regions near the top edge of the central cavity. On the left side, labels 27 and 6 are shown, with 6 encompassing a vertical stack of layers labeled 25 and 23. At the bottom left, label 23-2 points to a specific layer. Along the bottom edge of the central cavity, labels 20 and 19 are grouped under a bracket labeled 17. On the right side, labels 22 and 21 point to different parts of the outer structure. At the bottom right, label 16 points to a layer. Various other internal features and interfaces are delineated by solid and dashed lines.



Fig. 5

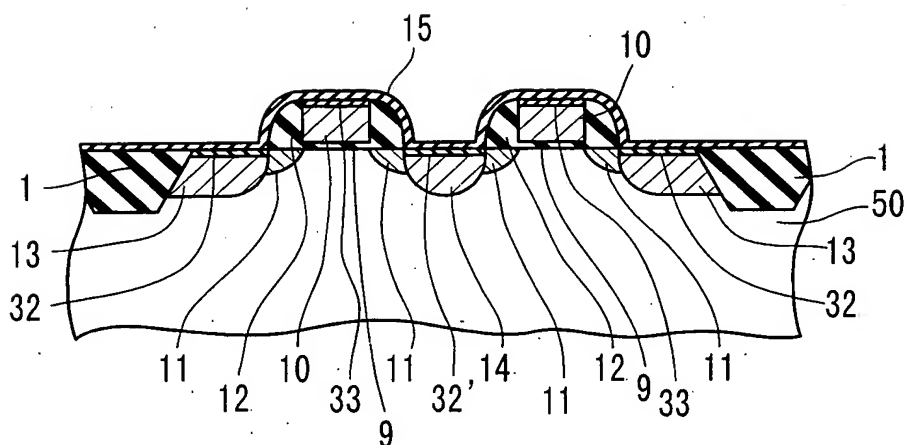
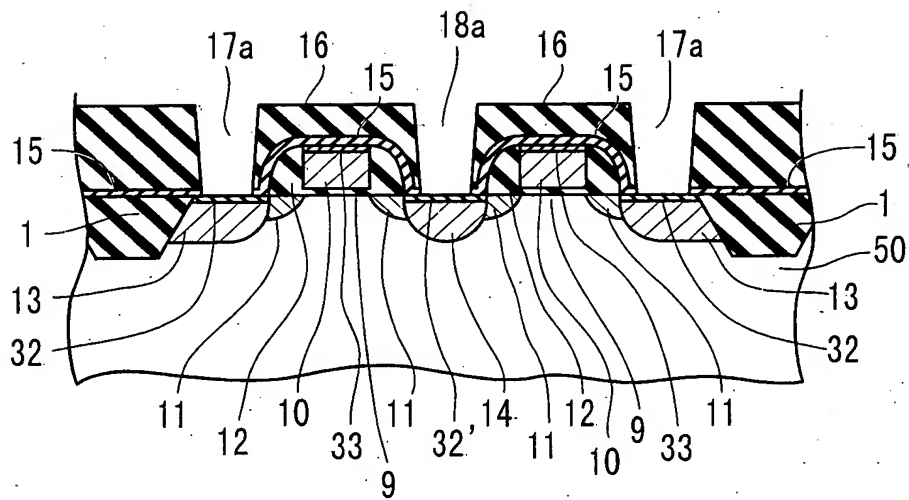




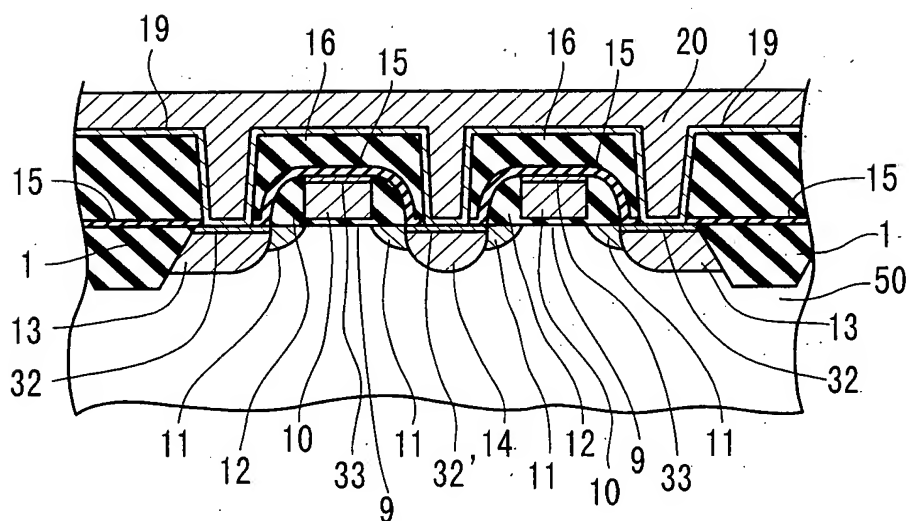
Fig. 6





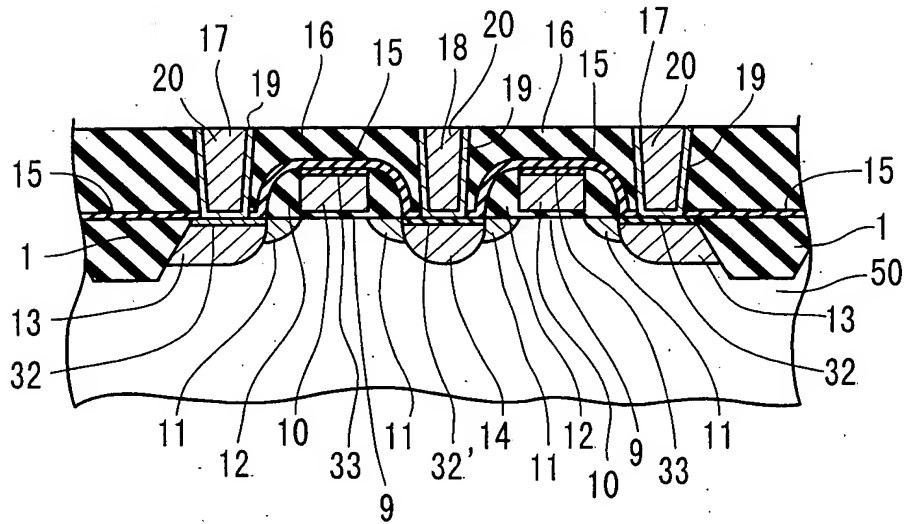
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APPLN No.: 10/068,893
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F i g . 7



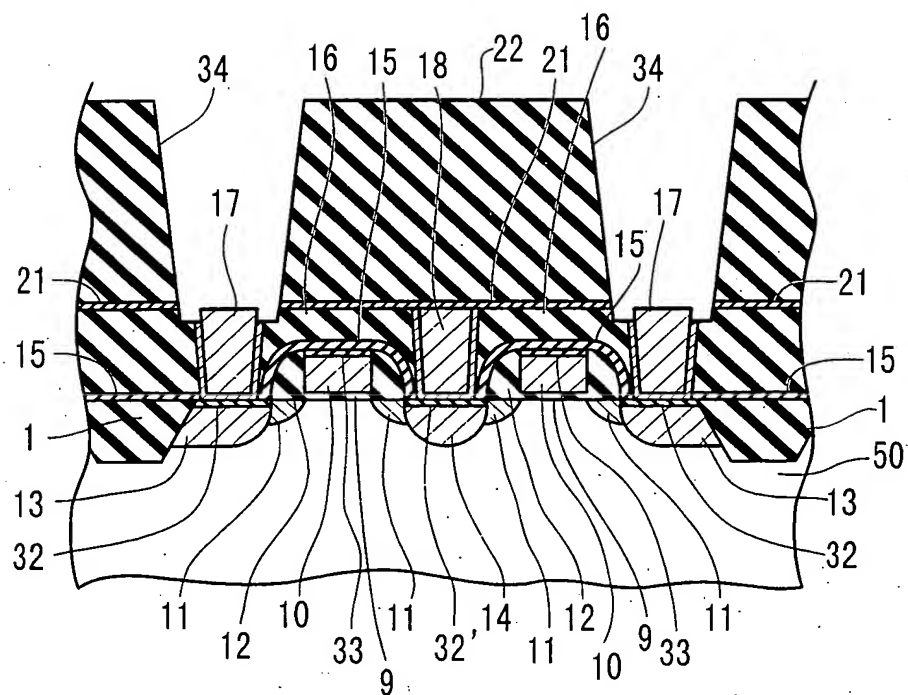


F i g . 8





F i g . 9





DOCKET No.: 8022-1003
APPLN No.: 10/068,893
REPLY TO NOTICE OF ALLOWABILITY OF: MAY 25, 2004
REPLACEMENT SHEET

Fig. 10

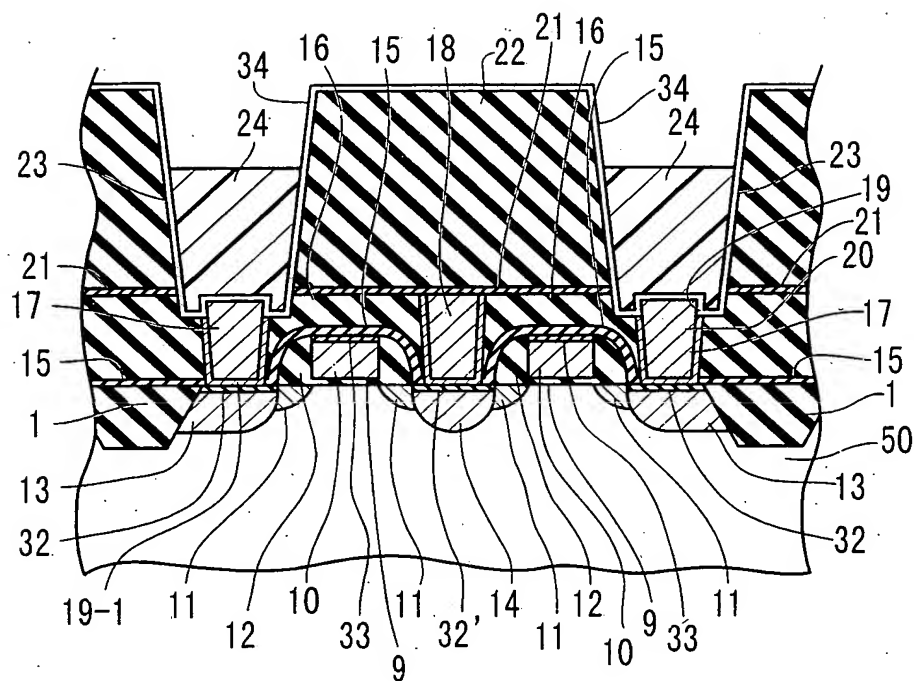
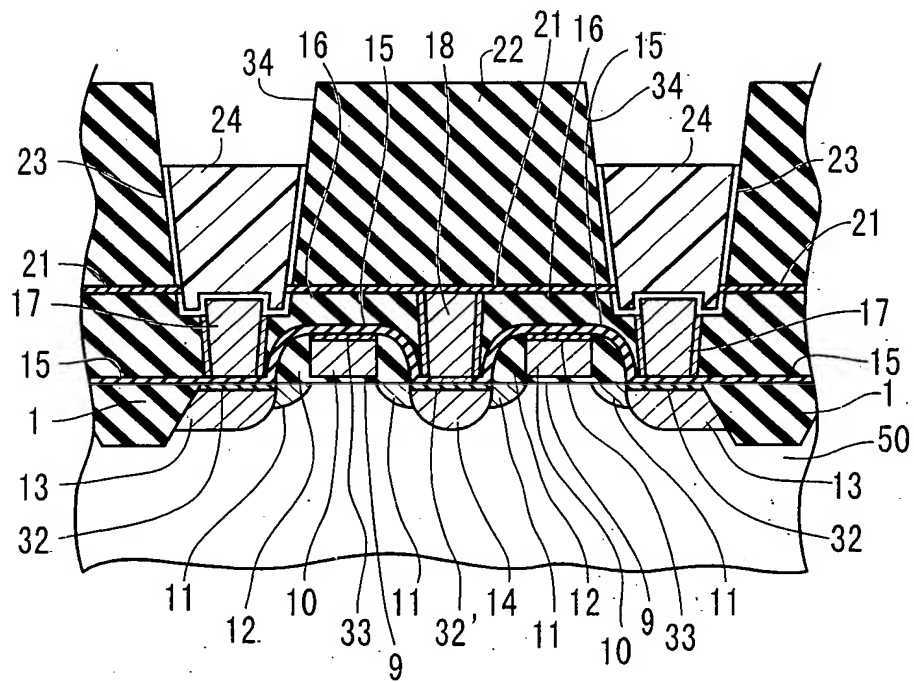




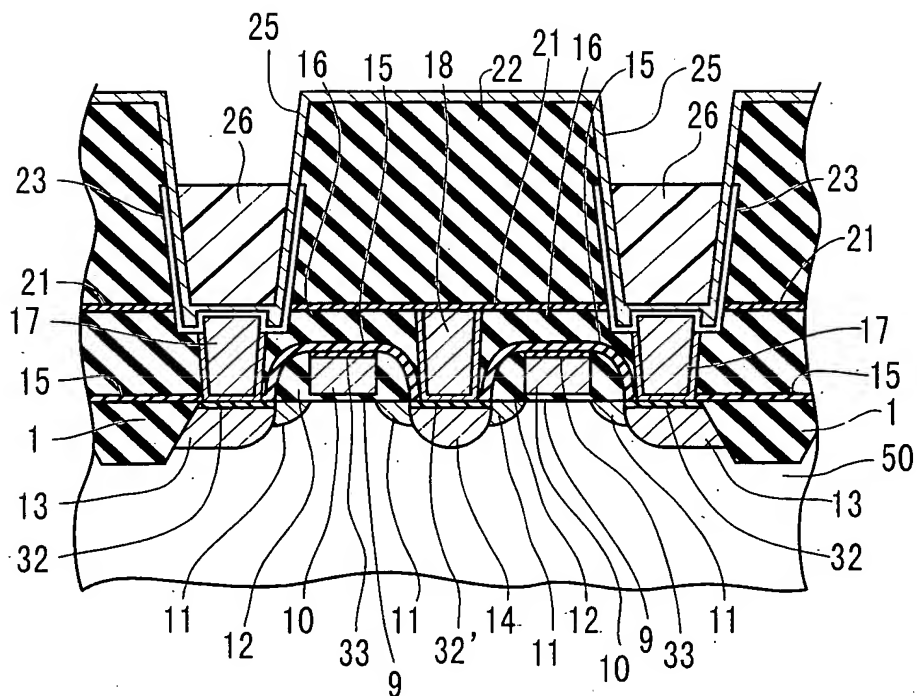
Fig. 11





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Fig. 12





F i g . 1 3

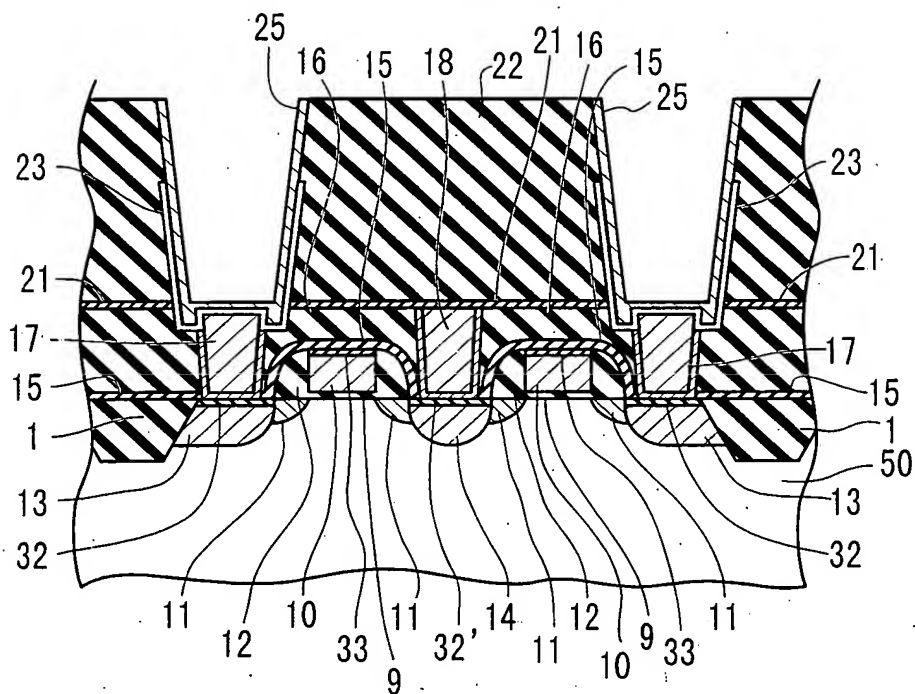




Fig. 14

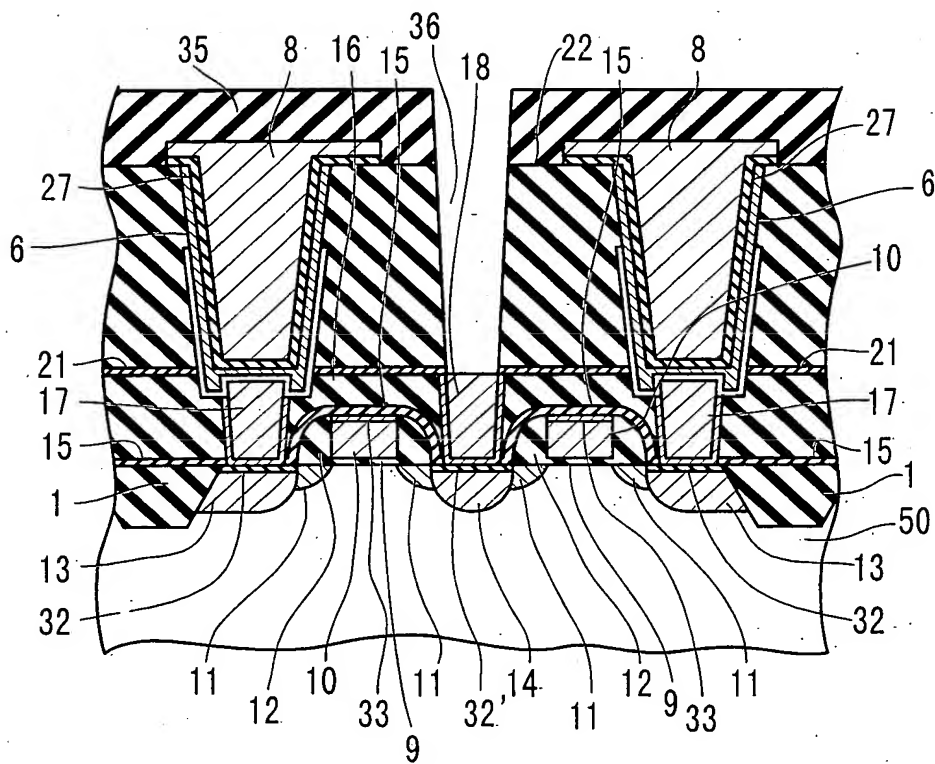




Fig. 15

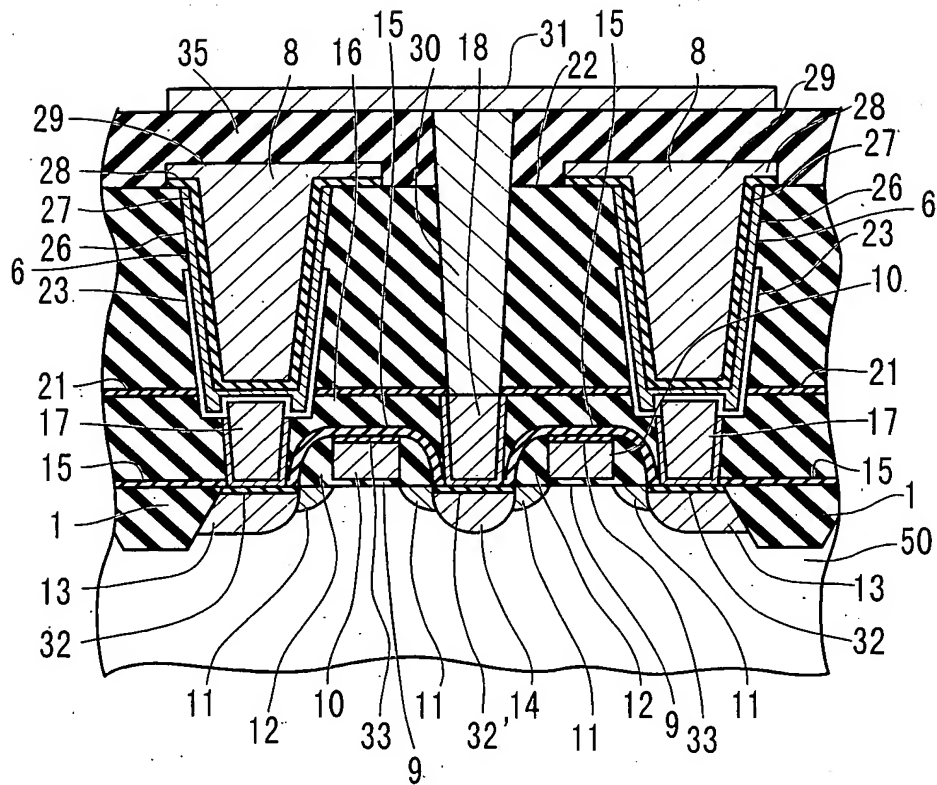


Fig. 16

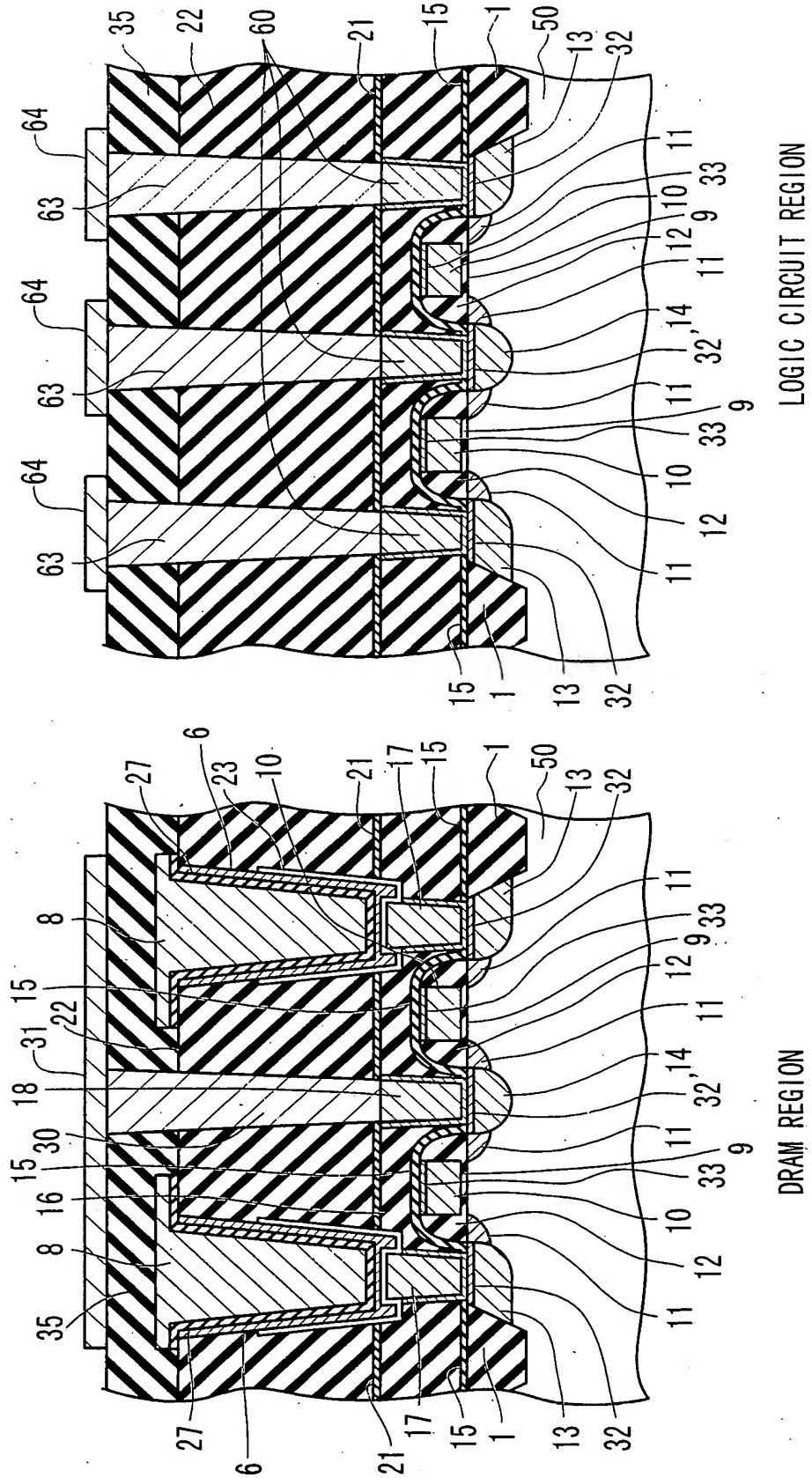
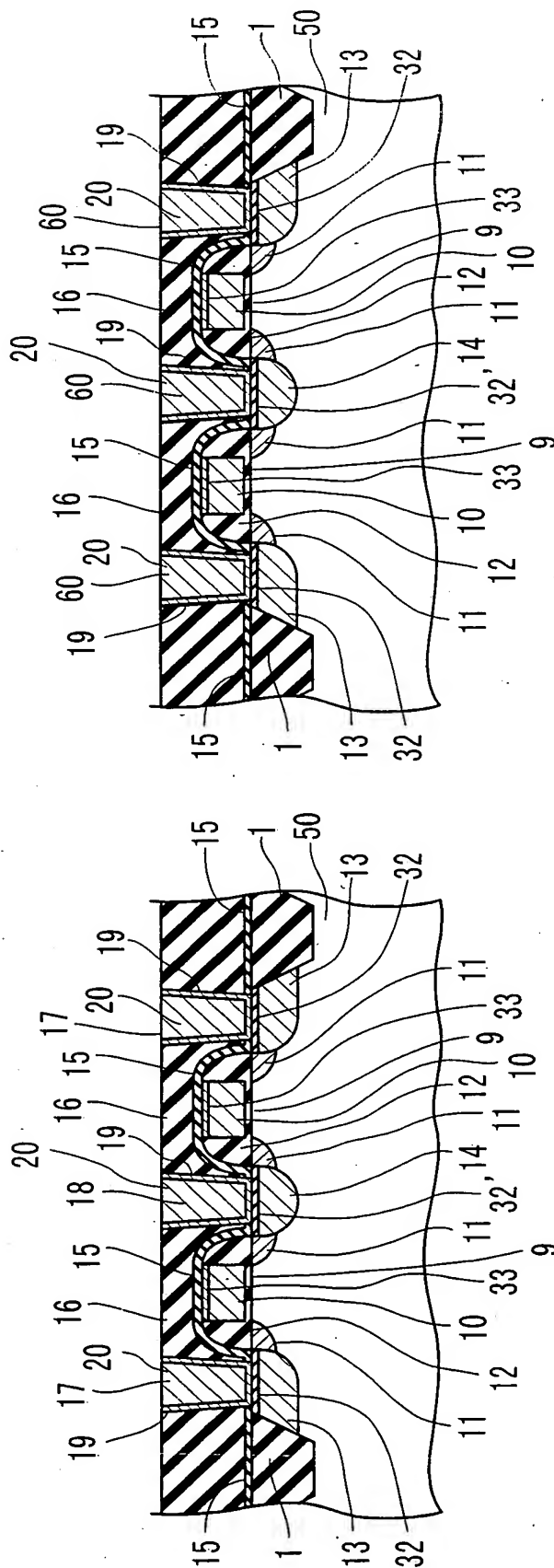




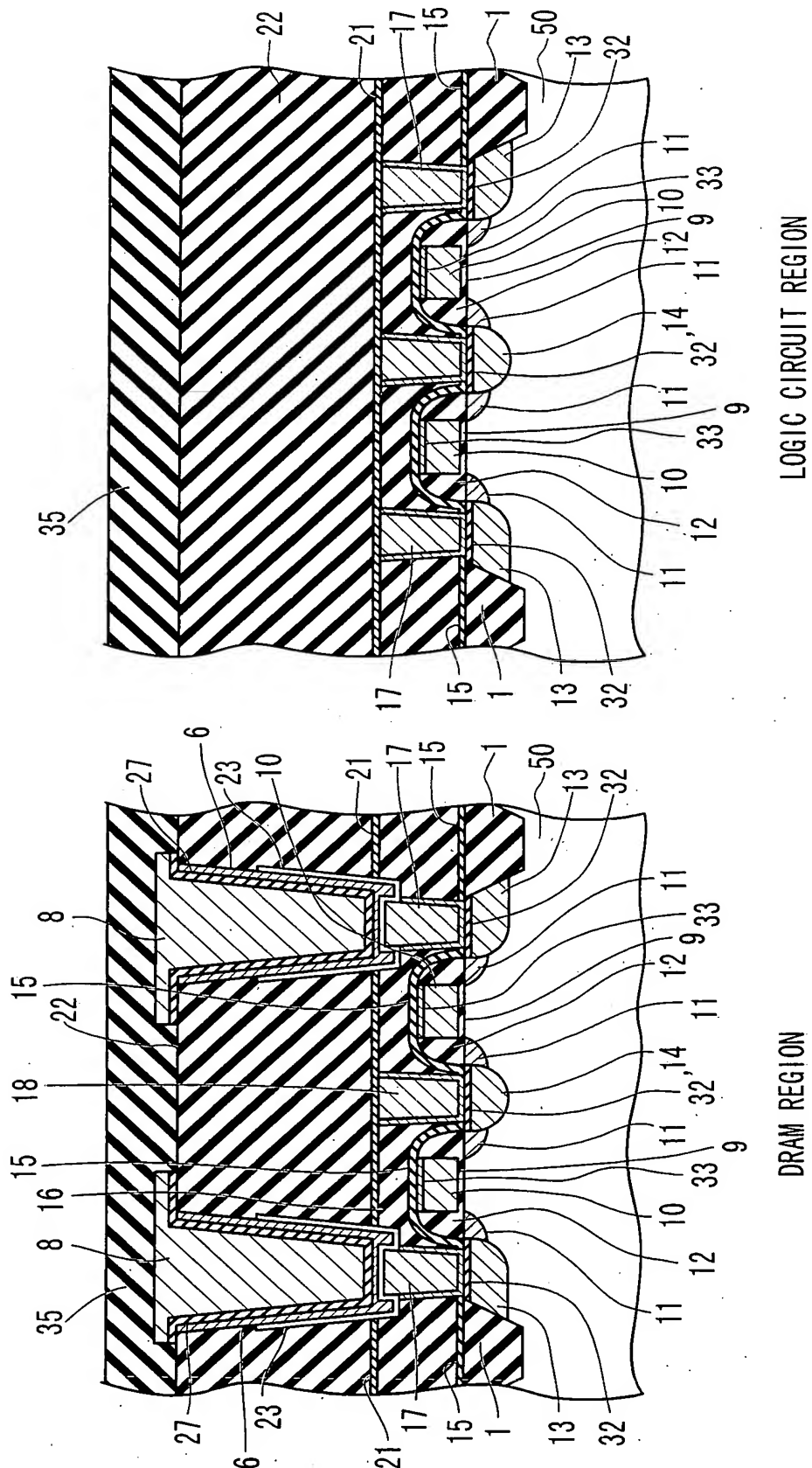
Fig. 17



LOGIC CIRCUIT REGION

DRAM REGION

Fig. 18





F i g . 1 9

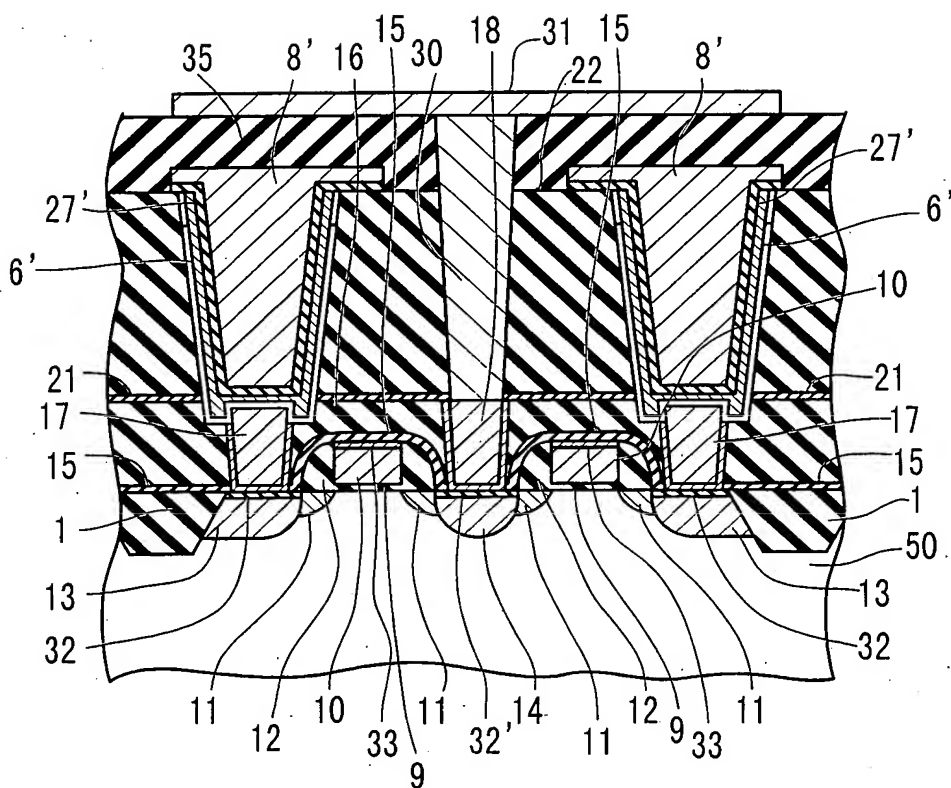
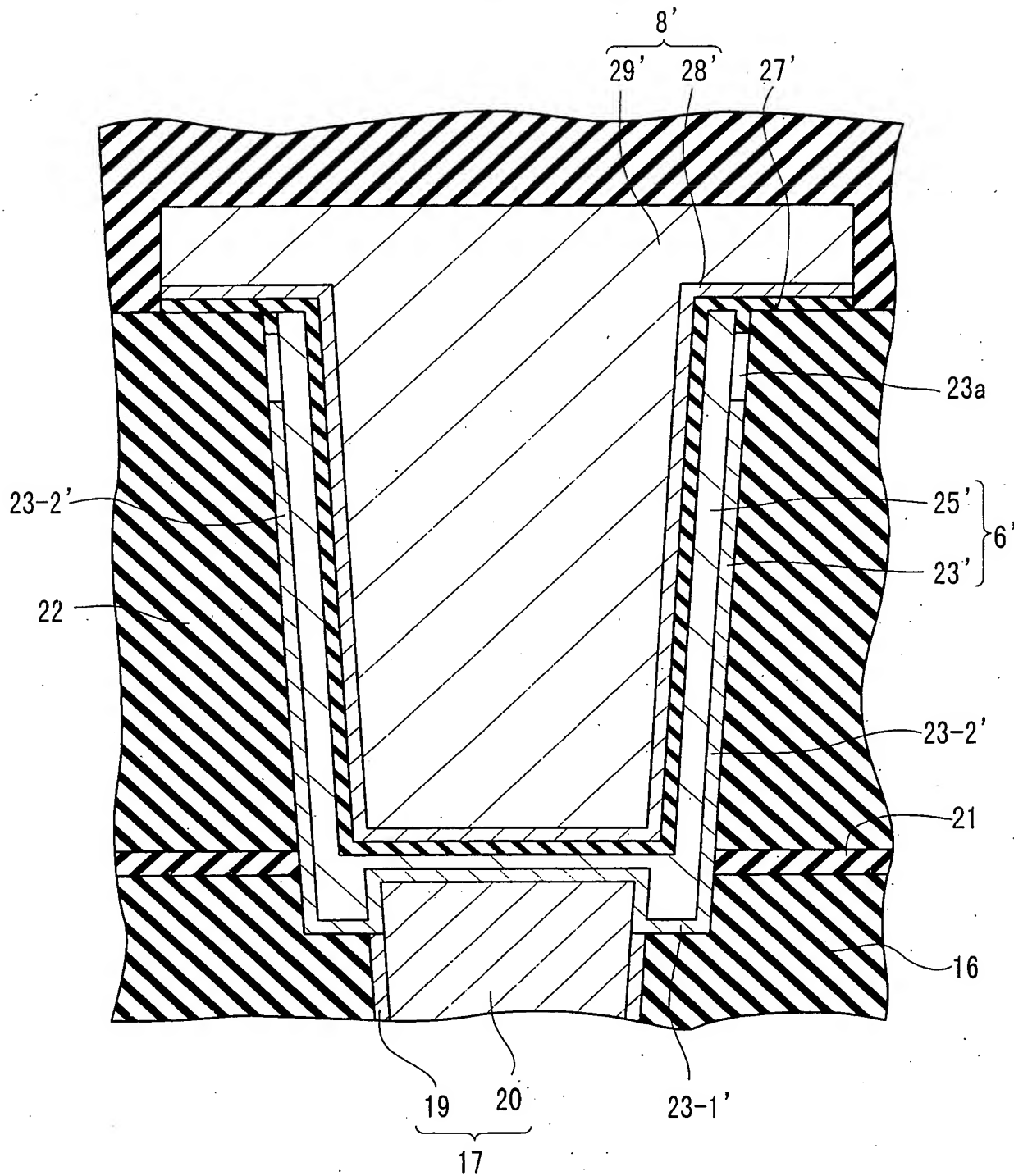




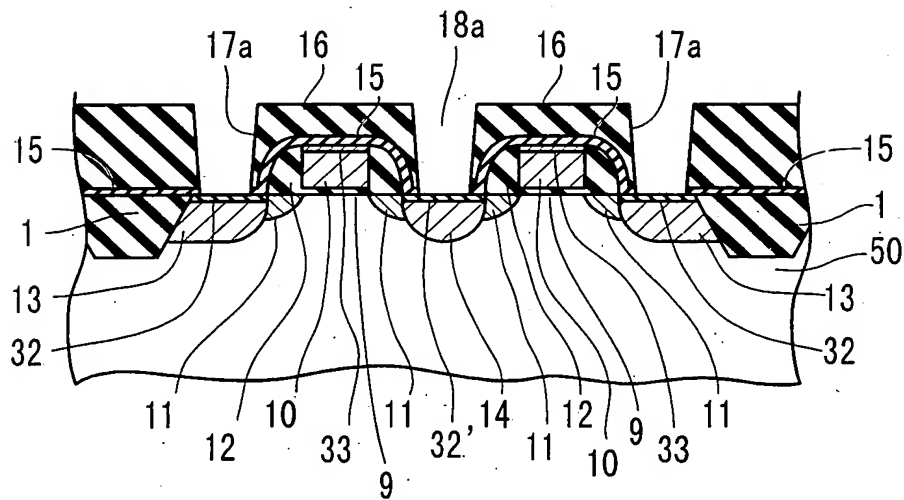
Fig. 20





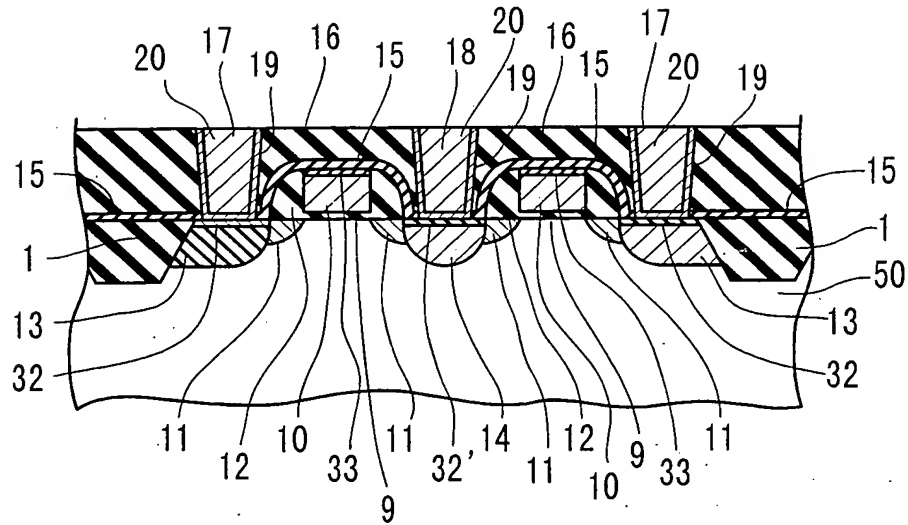
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APPLN No.: 10/068,893
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F i g . 2 1

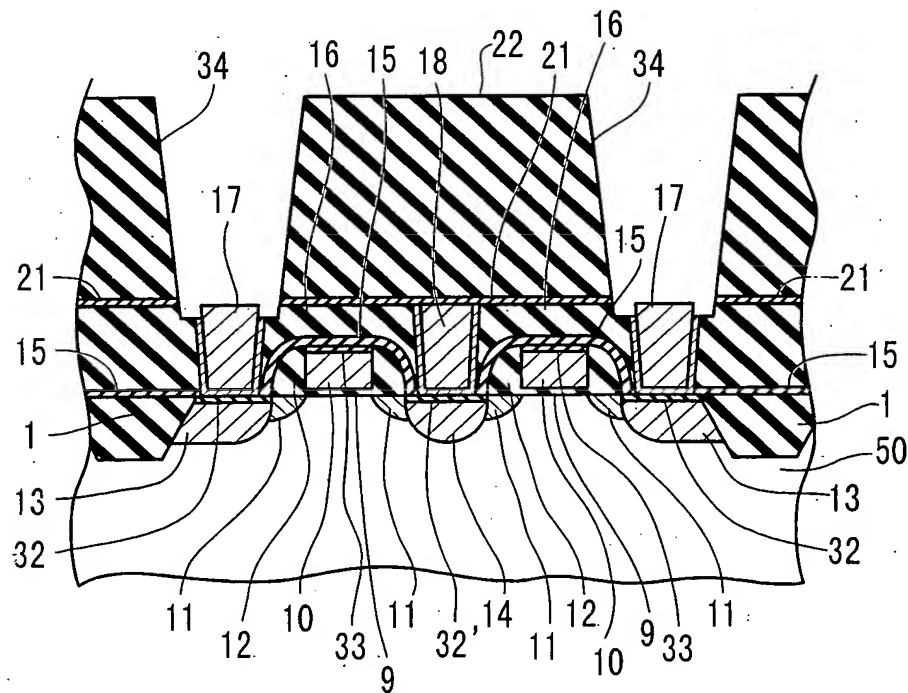




F i g . 2 2



F i g . 2 3



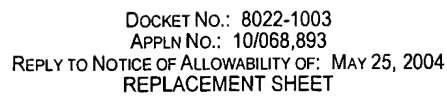




Fig. 25

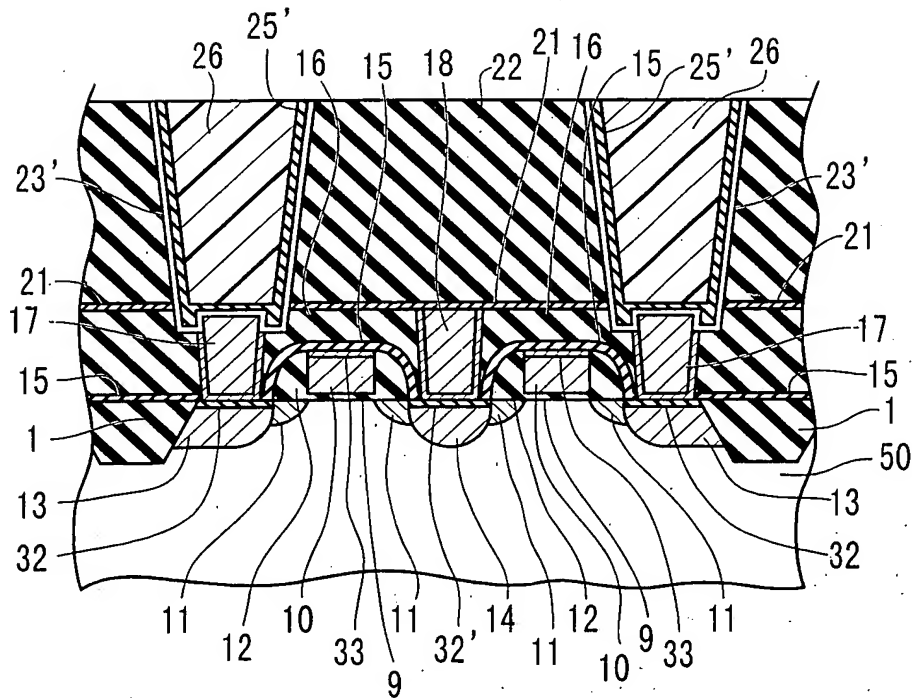


Fig. 26

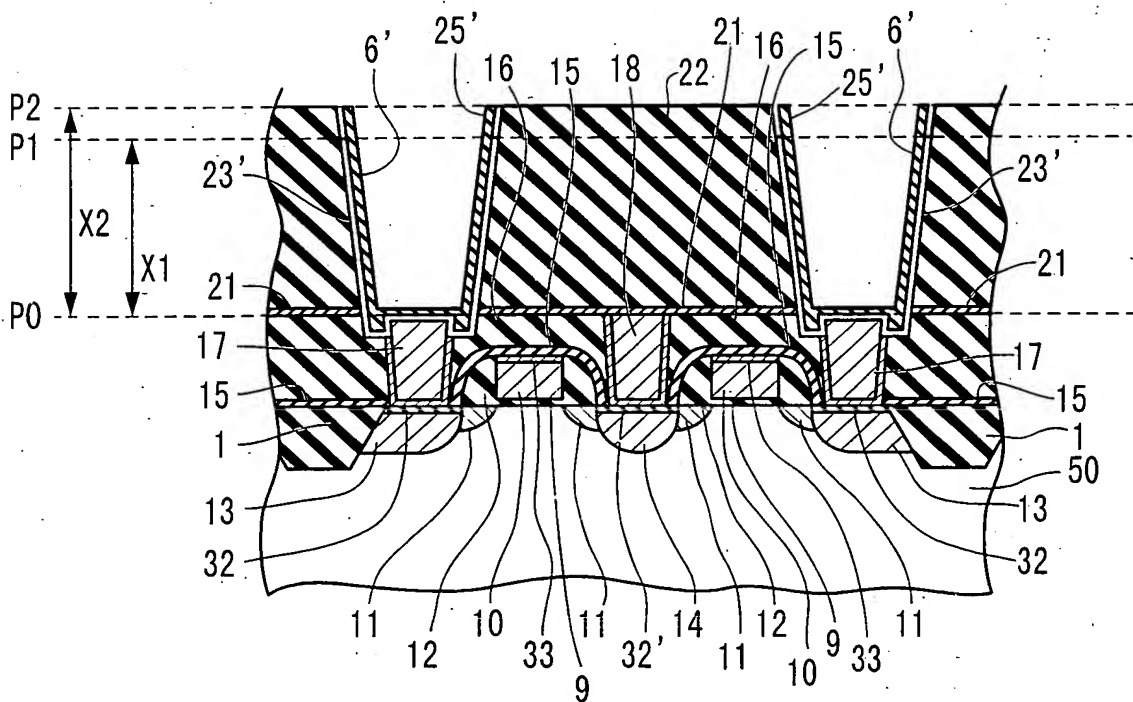
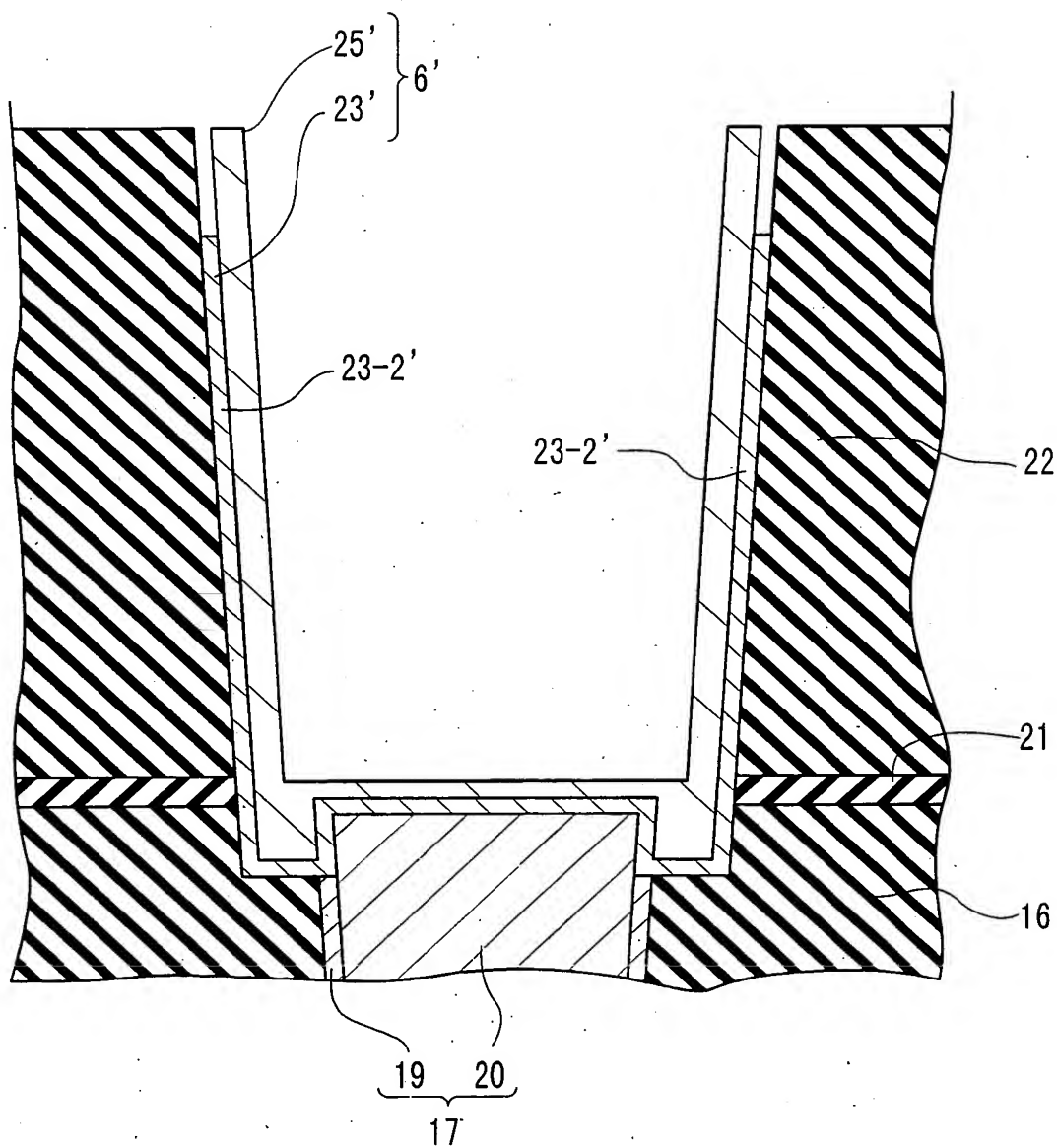




Fig. 27





F i g . 2 8

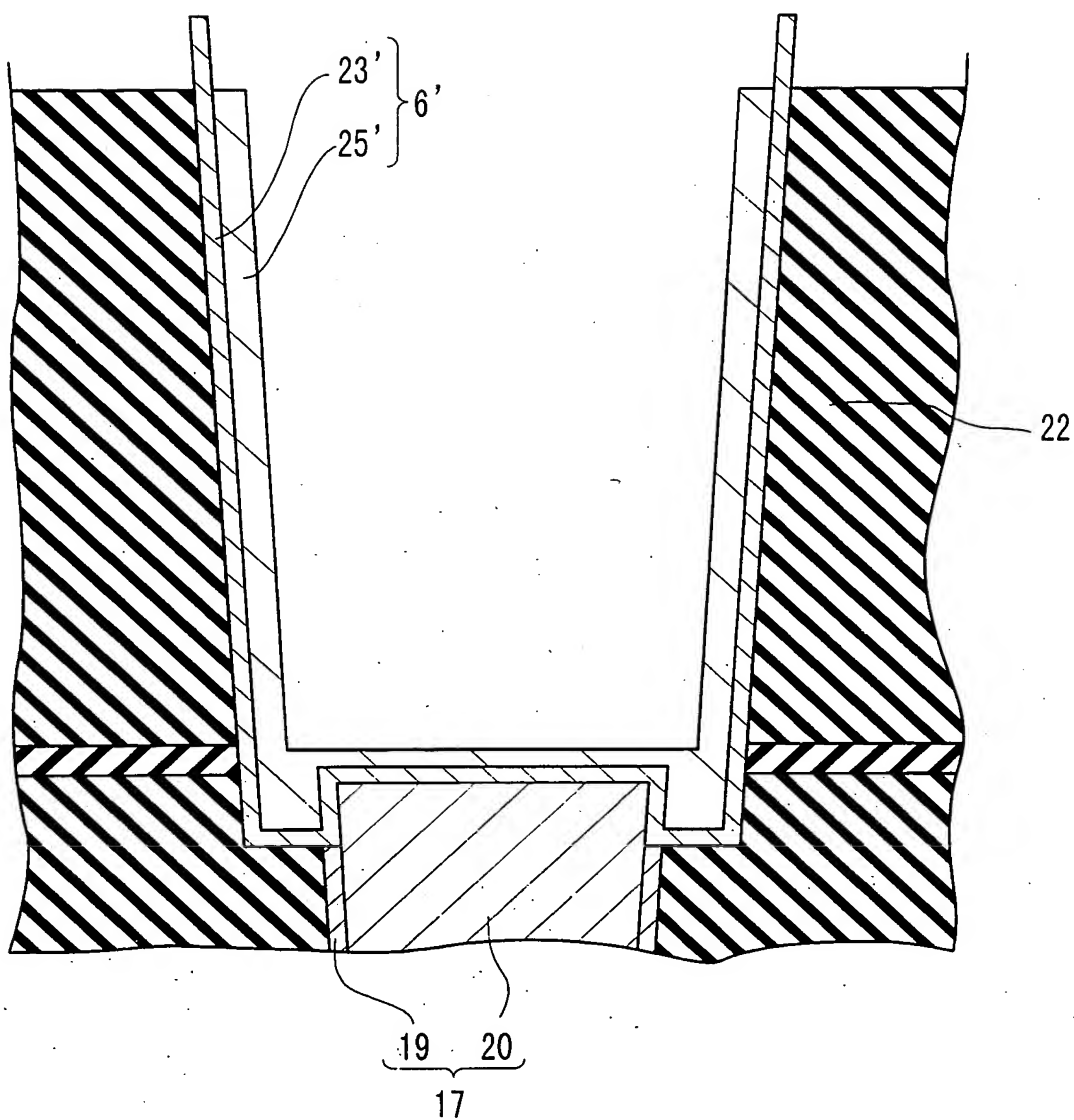




Fig. 29

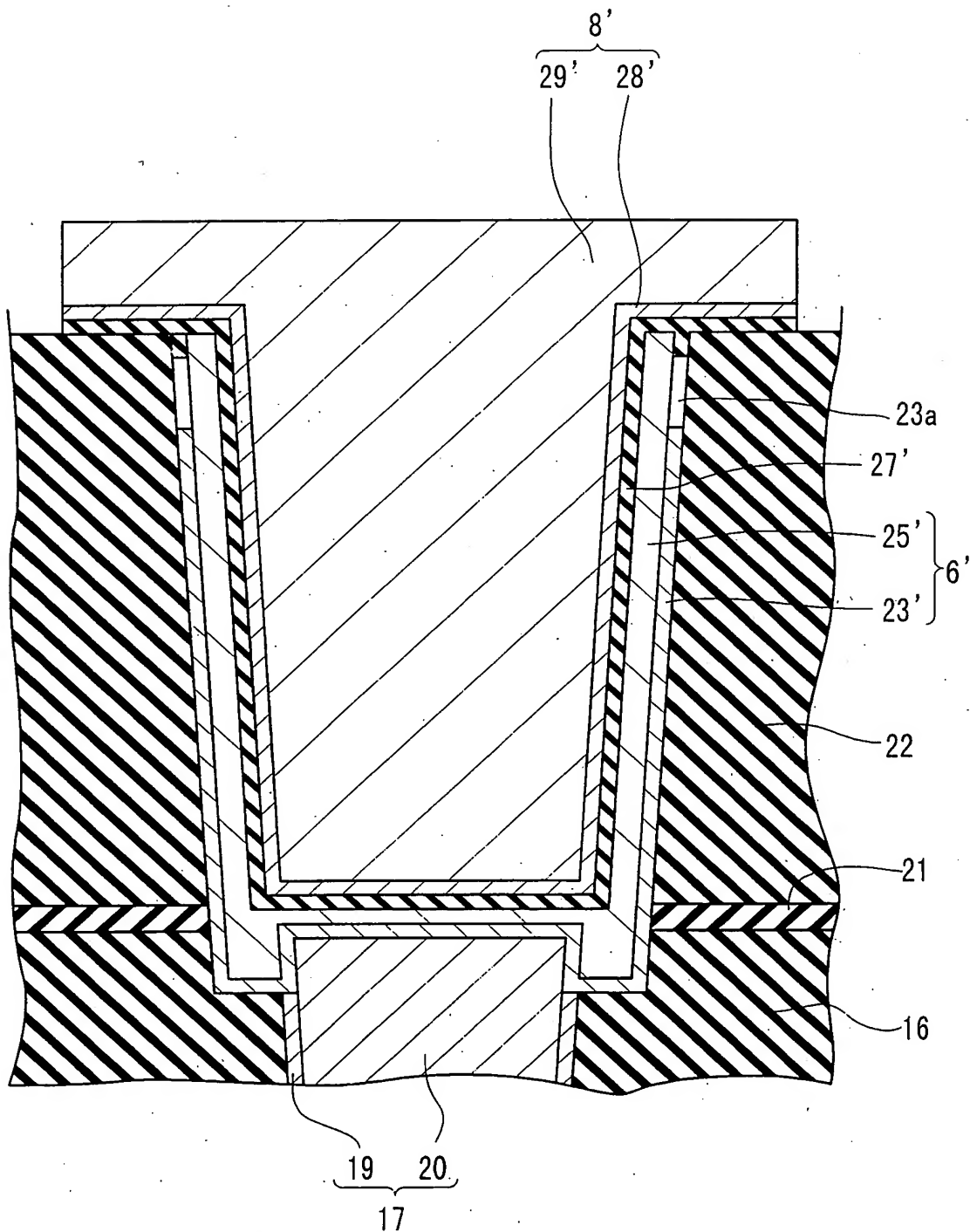




Fig. 30

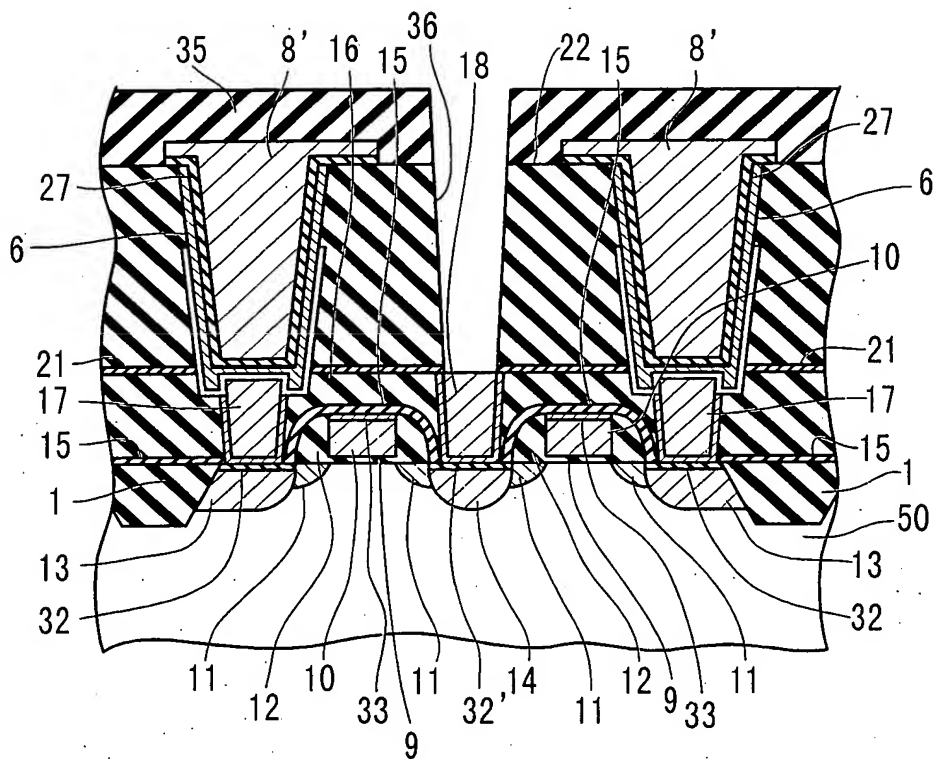




Fig. 31

